ABSTRACT

A semiconductor device includes a substrate including a key region, a dummy active pattern provided on the key region, a dummy channel pattern provided on the dummy active pattern, the dummy channel pattern including a first plurality of semiconductor patterns spaced apart from each other, an epitaxial pattern connected to the dummy channel pattern, and a first sub-key pattern provided on the dummy channel pattern. The first sub-key pattern encloses a top surface, a bottom surface, and side surfaces of each of the first plurality of semiconductor patterns.

FIG. 5A